

# DDTB (LO-R1) U

## PNP PRE-BIASED 500 mA SURFACE MOUNT TRANSISTOR

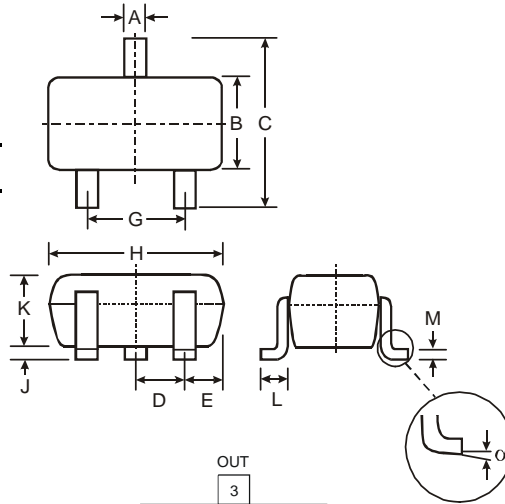
NEW PRODUCT

### Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDTD)
- Built-In Biasing Resistors
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 & 4)**

### Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Marking Information: See Table Below & Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	Min	Max
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
$\alpha$	0°	8°

All Dimensions in mm

P/N	R1 (NOM)	R2 (NOM)	Type Code
DDTB122LU	0.22K $\Omega$	10K $\Omega$	P75
DDTB142JU	0.47K $\Omega$	10K $\Omega$	P76
DDTB122TU	0.22K $\Omega$	OPEN	P77
DDTB142TU	0.47K $\Omega$	OPEN	P78

Schematic and Pin Configuration

### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage, (3) to (2)	V <sub>CC</sub>	-50	V
Input Voltage, (1) to (2)	V <sub>IN</sub>	+5 to -6	V
Input Voltage, (2) to (1)	V <sub>EBO (MAX)</sub>	-5	V
Output Current	I <sub>C</sub>	-500	mA
Power Dissipation	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

**Electrical Characteristics**

 @T<sub>A</sub> = 25°C unless otherwise specified

**R1, R2 Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DDTB122LU DDTB142JU	V <sub>I(off)</sub>	-0.3 -0.3	—	—	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	DDTB122LU DDTB142JU	V <sub>I(on)</sub>	—	—	-2.0 -2.0	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA
Output Voltage		V <sub>O(on)</sub>	—	—	-0.3V	V	I <sub>O</sub> /I <sub>I</sub> = -50mA/-2.5mA
Input Current	DDTB122LU DDTB142JU	I <sub>I</sub>	—	—	-28 -13	mA	V <sub>I</sub> = -5V
Output Current		I <sub>O(off)</sub>	—	—	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V
DC Current Gain	DDTB122LU DDTB142JU	G <sub>I</sub>	56 56	—	—	—	V <sub>O</sub> = -5V, I <sub>O</sub> = -50mA
Gain-Bandwidth Product*		f <sub>T</sub>	—	200	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100MHz

\* Transistor - For Reference Only

**Electrical Characteristics**

 @T<sub>A</sub> = 25°C unless otherwise specified

**R1 – Only Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV <sub>CB0</sub>	-50	—	—	V	I <sub>C</sub> = -50μA
Collector-Emitter Breakdown Voltage		BV <sub>CEO</sub>	-40	—	—	V	I <sub>C</sub> = -1mA
Emitter-Base Breakdown Voltage	DDTB122TU DDTB142TU	BV <sub>EBO</sub>	-5	—	—	V	I <sub>E</sub> = -50μA I <sub>E</sub> = -50μA
Collector Cutoff Current		I <sub>CB0</sub>	—	—	-0.5	μA	V <sub>CB</sub> = -50V
Emitter Cutoff Current	DDTB122TU DDTB142TU	I <sub>EBO</sub>	— —	—	-0.5 -0.5	μA	V <sub>EB</sub> = -4V
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	—	—	-0.3	V	I <sub>C</sub> = -50mA, I <sub>B</sub> = -2.5mA
DC Current Transfer Ratio	DDTB122TU DDTB142TU	h <sub>FE</sub>	100 100	250 250	600 600	—	I <sub>C</sub> = -5mA, V <sub>CE</sub> = -5V
Gain-Bandwidth Product*		f <sub>T</sub>	—	200	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz

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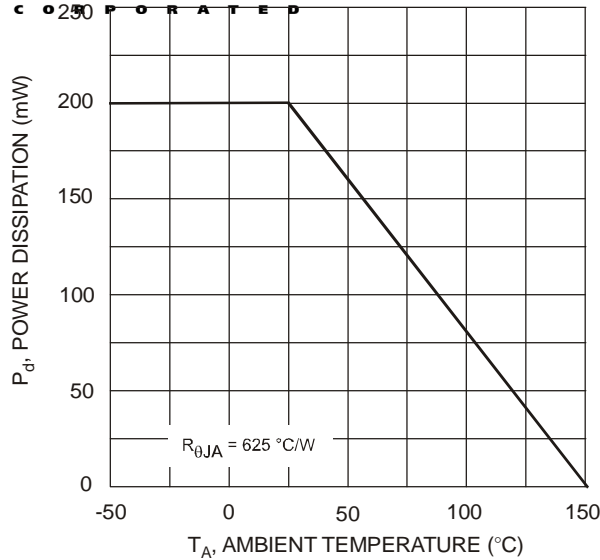


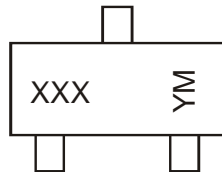
Fig. 1 Power Derating Curve

## Ordering Information (Note 4 & 5)

Device	Packaging	Shipping
DDTB122LU-7-F	SOT-323	3000/Tape & Reel
DDTB142JU-7-F	SOT-323	3000/Tape & Reel
DDTB122TU-7-F	SOT-323	3000/Tape & Reel
DDTB142TU-7-F	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



XXX = Product Type Marking Code (See Page 1)  
 YM = Date Code Marking  
 Y = Year ex: T = 2006  
 M = Month ex: 9 = September

### Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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